

SKM50GB063D



SEMITRANS® 2

Superfast NPT-IGBT Modules

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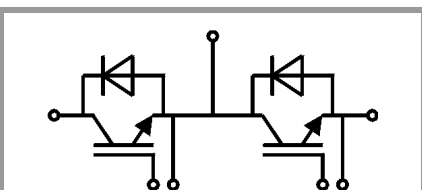
Target Data

Features

- NPT = non punch-through IGBT technology
- High short circuit capability, self limiting to 6 x IC
- Pos. temp.-coeff. of VCEsat
- Isolated copper baseplate

Typical Applications*

- Switched mode power supplies
- UPS
- Three phase inverters for servo / AC motor speed control



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Absolute Maximum Ratings				
Symbol	Conditions	Values	Unit	
IGBT				
V _{CEs}	T _j = 25 °C	600	V	
I _C	T _j = 150 °C	T _c = 25 °C	70	A
		T _c = 75 °C	51	A
I _{Cnom}		50	A	
I _{CRM}	I _{CRM} = 2xI _{Cnom}	100	A	
V _{GES}		-20 ... 20	V	
t _{psc}	V _{CC} = 300 V	T _j = 125 °C	10	µs
	V _{GE} ≤ 20 V			
	V _{CEs} ≤ 600 V			
T _j		-55 ... 150	°C	
Inverse diode				
I _F		T _c = 25 °C	75	A
		T _c = 80 °C	45	A
I _{Fnom}		50	A	
I _{FRM}	I _{FRM} = 2xI _{Fnom}	100	A	
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		A	
T _j		-40 ... 150	°C	
Module				
I _{t(RMS)}	T _{terminal} < 80 °C	200	A	
T _{stg}		-40 ... 125	°C	
V _{isol}	AC sinus 50Hz, t = 1 min	2500	V	

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
V _{CE(sat)}	I _C = 50 A V _{GE} = 15 V chipelevel	T _j = 25 °C	2.1	2.5	V
		T _j = 125 °C	2.4	2.8	V
V _{CE0}		T _j = 25 °C	1.05	1.3	V
		T _j = 125 °C	1	1.2	V
r _{CE}	V _{GE} = 15 V	T _j = 25 °C	21.0	24.0	mΩ
		T _j = 125 °C	28.0	32.0	mΩ
V _{GE(th)}	V _{GE} =V _{CE} , I _C = 1 mA	4.5	5.5	6.5	V
I _{CEs}	V _{GE} = 0 V V _{CE} = 600 V	T _j = 25 °C	0.1	0.3	mA
					mA
C _{ies}	V _{CE} = 25 V		2.2		nF
C _{oes}	V _{GE} = 0 V				nF
C _{res}			0.2		nF
Q _G	V _{GE} = - 8 V...+ 20 V				nC
R _{Gint}	T _j = 25 °C				Ω
t _{d(on)}	V _{CC} = 300 V	T _j = 125 °C	50		ns
t _r	I _C = 50 A V _{GE} = ±15 V	T _j = 125 °C	40		ns
E _{on}	R _{G on} = 22 Ω	T _j = 125 °C	2.5		mJ
t _{d(off)}	R _{G off} = 22 Ω	T _j = 125 °C	300		ns
t _f		T _j = 125 °C	30		ns
E _{off}		T _j = 125 °C	1.8		mJ
R _{th(j-c)}	per IGBT			0.5	K/W



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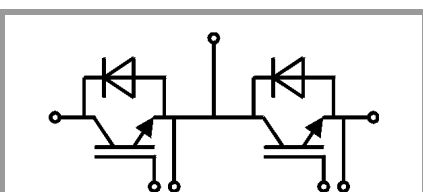
Features

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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	$I_F = 50\text{ A}$ $V_{GE} = 0\text{ V}$ chip	$T_j = 25\text{ °C}$		1.35	1.60	V
		$T_j = 125\text{ °C}$		1.35	1.60	V
V_{F0}		$T_j = 25\text{ °C}$		1.05	1.2	V
		$T_j = 125\text{ °C}$		0.9	1	V
r_F		$T_j = 25\text{ °C}$		6.0	8.0	mΩ
		$T_j = 125\text{ °C}$		9.0	12.0	mΩ
I_{RRM}	$I_F = 50\text{ A}$ $di/dt_{off} = 50\text{ A}/\mu\text{s}$ $V_{GE} = \pm 15\text{ V}$ $V_{CC} = 300\text{ V}$	$T_j = 125\text{ °C}$		31		A
Q_{rr}		$T_j = 125\text{ °C}$		3.2		μC
E_{rr}		$T_j = 125\text{ °C}$		0.48		mJ
$R_{th(j-c)}$	per diode				1	K/W
Module						
L_{CE}					30	nH
$R_{CC'+EE'}$	terminal-chip	$T_C = 25\text{ °C}$		0.65		mΩ
		$T_C = 125\text{ °C}$		1		mΩ
$R_{th(c-s)}$	per module			0.04	0.05	K/W
M_s	to heat sink M6		3		5	Nm
M_t		to terminals M5	2.5		5	Nm
						Nm
w					160	g



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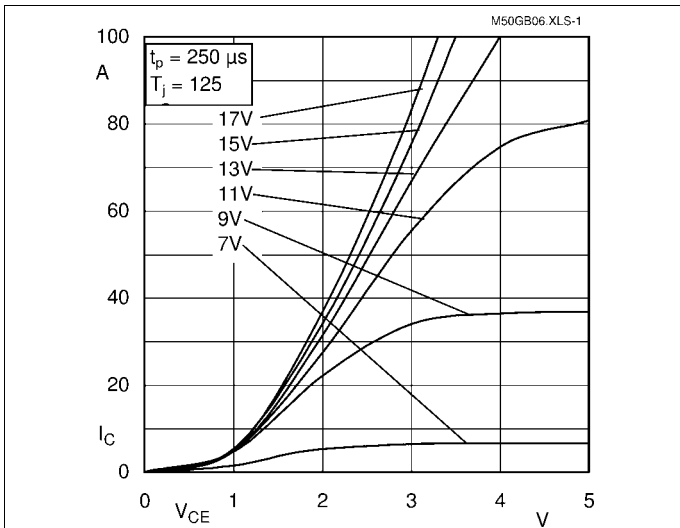


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

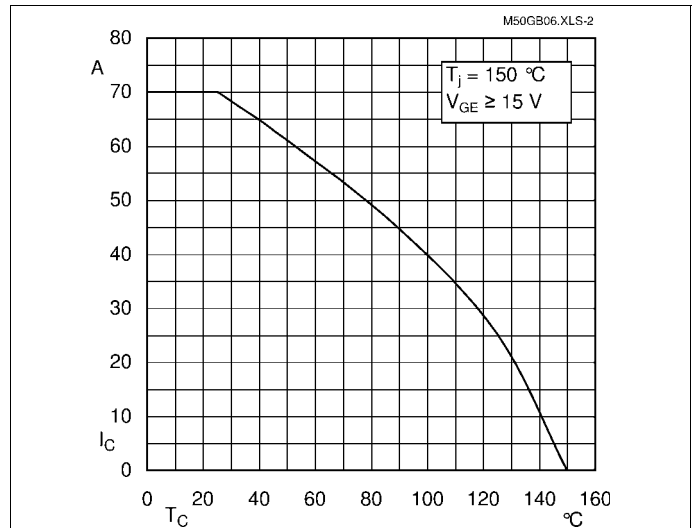


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

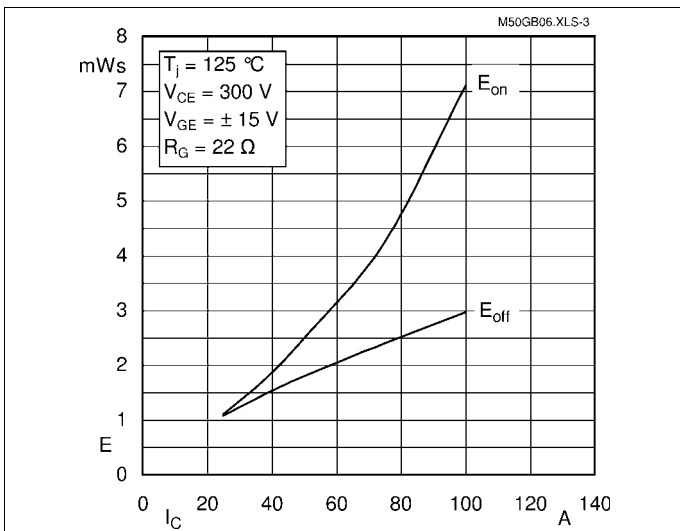


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

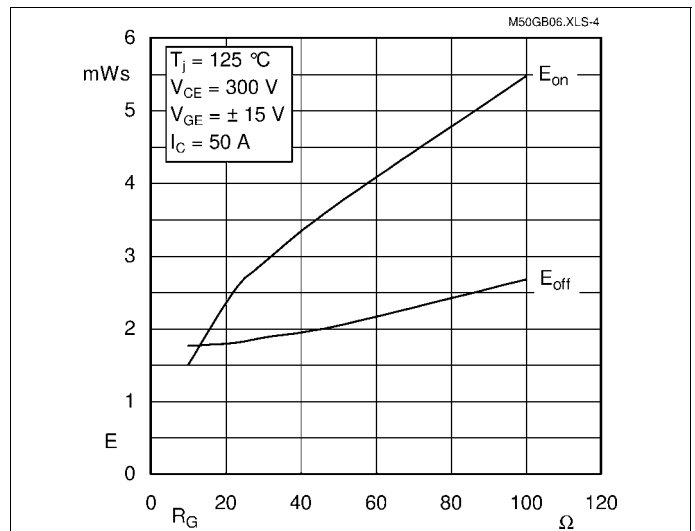


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

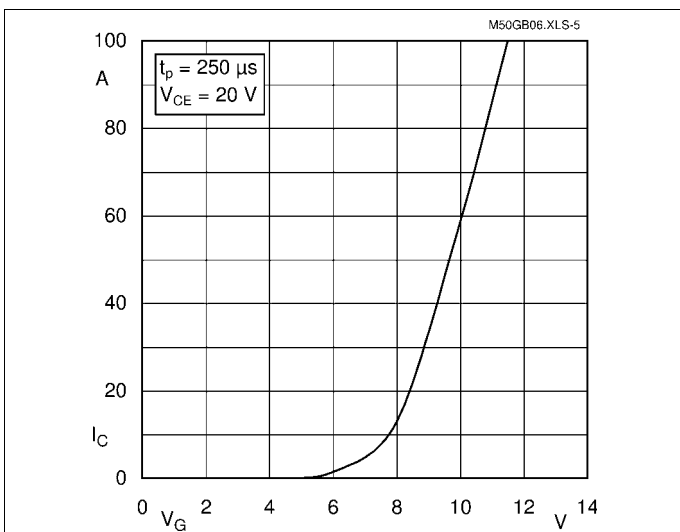


Fig. 5: Typ. transfer characteristic

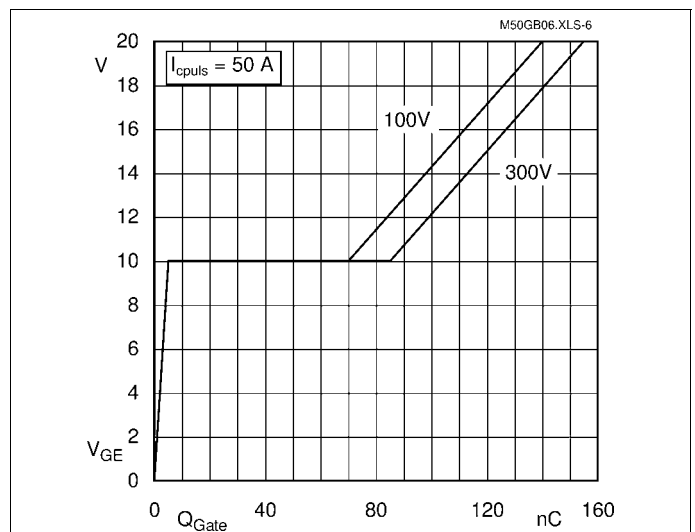


Fig. 6: Typ. gate charge characteristic

